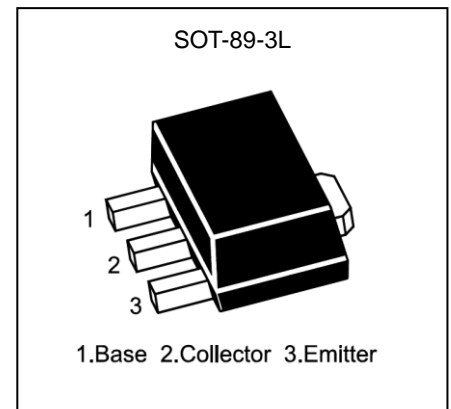




BCX56 Transistor(NPN)

Feature

- Low Voltage
- High Current



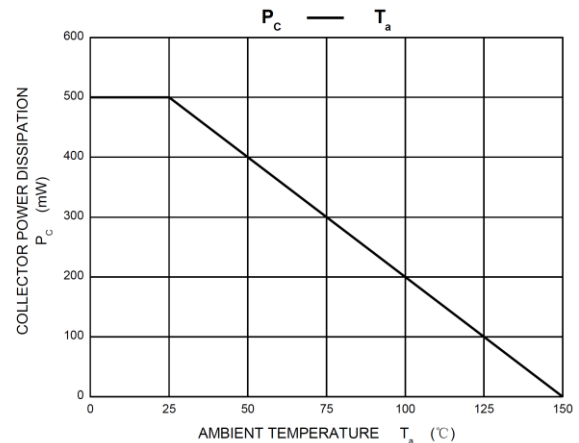
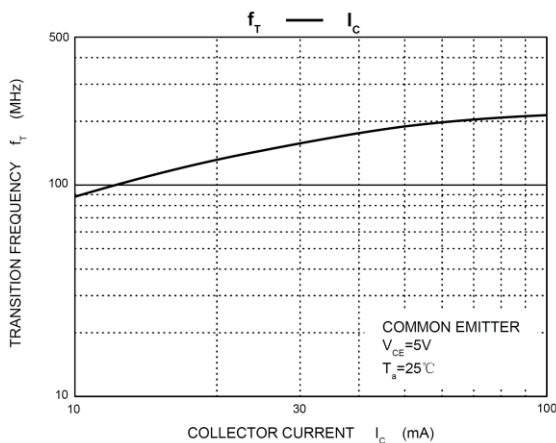
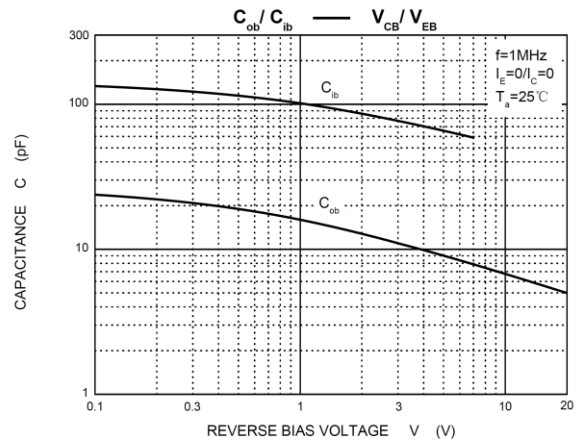
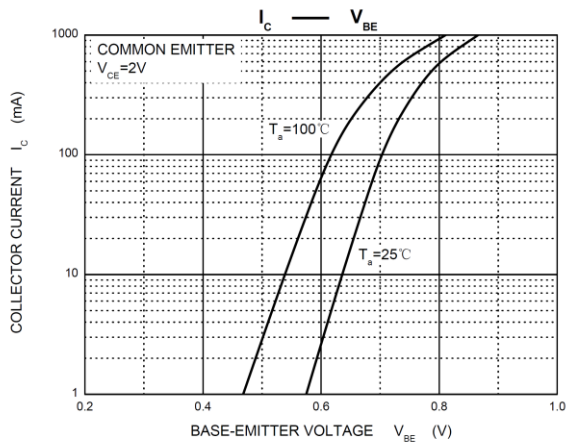
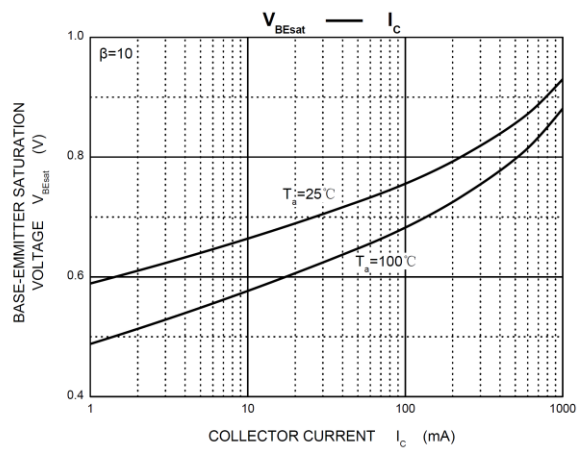
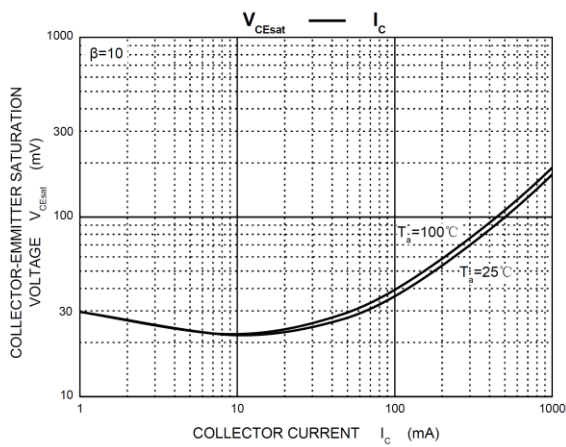
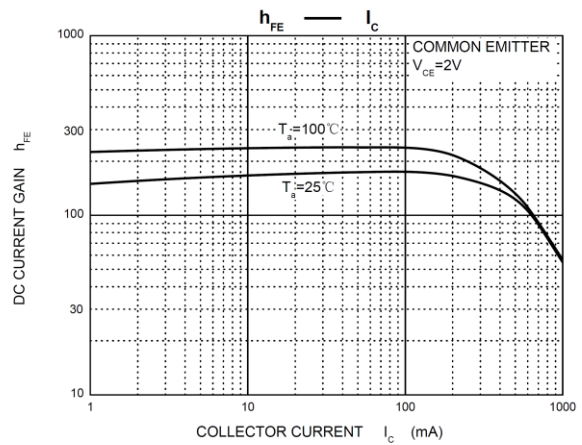
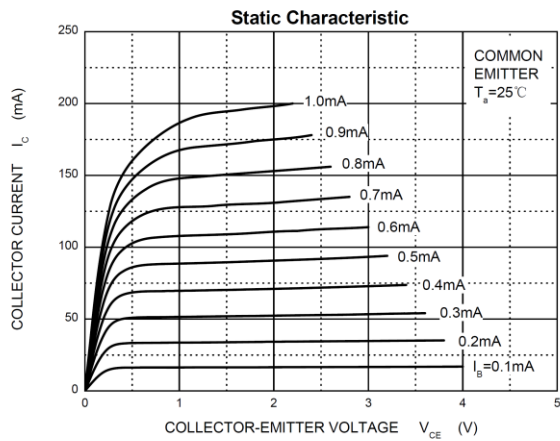
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

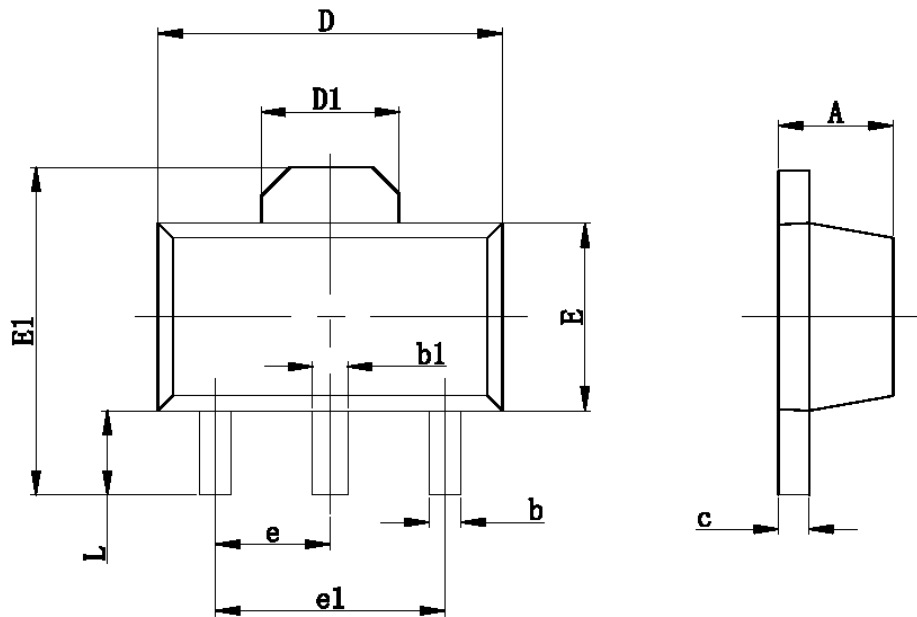
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _c	1	A
Peak Collect Current	I _{CM}	1.5	A
Power Dissipation	P _d	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =100μA, I _E =0	100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =1mA, I _B =0	80			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _c =0	5			V
Base cut-off current	I _{CB0}	V _{CB} =30V, I _E =0V			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _c =0			100	nA
DC current gain	h _{FE}	V _{CE} =2V, I _c =5mA	40			
		V _{CE} =2V, I _c =150mA BCX56-10	63		160	
		V _{CE} =2V, I _c =150mA BCX56-16	100		250	
		V _{CE} =2V, I _c =500mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA, I _B =50mA			0.5	V
Base-emitter saturation voltage	V _{BE}	I _c =500mA, V _{CE} =2V			1.0	V
Transition frequency	f _T	V _{CE} = 5V, I _c =50mA, f=100MHz	100			MHZ
Collector Capacitance	C _C	V _{CB} = 10V, f=1MHz		6		pF

Typical Characteristics



SOT-89-3L Package Outline Dimensions


Symbol	Dimensions in millimeters		Dimensions in inches	
	Min.	Max.	Min.	Max.
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550REF		0.061REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500TYP		0.060TYP	
e1	3.000TYP		0.118TYP	
L	0.900	1.200	0.035	0.047

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)